US 20240237330A1

(19) United States

(12) Patent Application Publication (10) Pub. No.: US 2024/0237330 A1

Greenlee et al. (43) Pub. Date: Jul. 11, 2024

(54) **ARRAY OF CAPACITORS, ARRAY OF MEMORY CELLS, AND METHODS USED IN FORMING AN ARRAY OF CAPACITORS**

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(21) Appl. No.: **18/407,675**

(22) Filed: **Jan. 9, 2024**

Related U.S. Application Data

(60) Provisional application No. 63/438,304, filed on Jan. 11, 2023.

Publication Classification

(51) **Int. Cl.**

H10B 12/00 (2006.01)

G11C 5/06 (2006.01)

(52) **U.S. Cl.**

CPC ***H10B 12/31*** (2023.02); ***G11C 5/063*** (2013.01); ***H01L 28/91*** (2013.01); ***H10B 12/482*** (2023.02); ***H10B 12/488*** (2023.02)

(57) **ABSTRACT**

A method used in forming an array of capacitors comprises forming horizontally-spaced openings into sacrificial material and through insulative material that is between a top and bottom of the sacrificial material. The insulative material at least predominately comprises at least one of a silicon nitride, a silicon boronitride, and a silicon carbonitride. The insulative material with horizontally-spaced openings therethrough comprises an insulative horizontal lattice. An insulative lining is deposited within the horizontally-spaced openings and directly above the sacrificial material. The insulative lining at least predominately comprises at least one of a silicon oxide and a silicon oxynitride. During the depositing, the insulative lining is intermittently exposed to a nitrogen-containing plasma. First capacitor electrodes that are individually within individual of the horizontally-spaced openings are formed laterally over the insulative lining that is in the horizontally-spaced openings. The sacrificial material is removed and a capacitor insulator is formed over the first capacitor electrodes and the insulative horizontal lattice. Second-capacitor-electrode material is formed over the capacitor insulator. Structure independent of method is disclosed.